

**4N60K-MK**

Preliminary

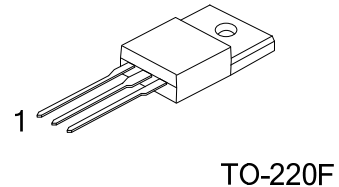
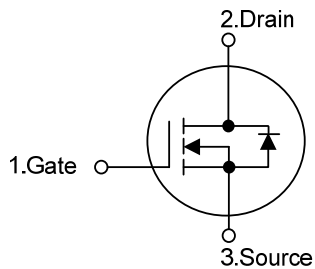
Power MOSFET

**4A, 600V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **4N60K-MK** is a high voltage power MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in power supplies, PWM motor controls, high efficient DC to DC converters and bridge circuits.

FEATURES

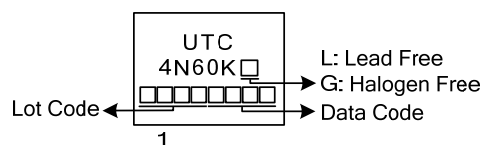
- * $R_{DS(ON)} < 2.5\Omega$ @ $V_{GS} = 10V$
- * Fast Switching Capability
- * Avalanche Energy Specified
- * Improved dv/dt Capability, high Ruggedness

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
4N60KL-TF3-T	4N60KG-TF3-T	TO-220F	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

4N60KL-TF3-T (1) Packing Type (2) Package Type (3) Lead Free		(1) T: Tube (2) TF3: TO-220F (3) L: Lead Free, G: Halogen Free
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MARKING

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V _{DSS}	600	V
Gate-Source Voltage		V _{GSS}	±30	V
Avalanche Current (Note 2)		I _{AR}	4.4	A
Drain Current	Continuous	I _D	4.0	A
	Pulsed (Note 2)	I _{DM}	16	A
Avalanche Energy	Single Pulsed (Note 3)	E _{AS}	160	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	4.5	V/ns
Power Dissipation		P _D	36	W
Derate above 25°C			0.288	W/°C
Junction Temperature		T _J	+150	°C
Operating Temperature		T _{OPR}	-55 ~ +150	°C
Storage Temperature		T _{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L = 20\text{mH}$, $I_{AS} = 4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 4.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

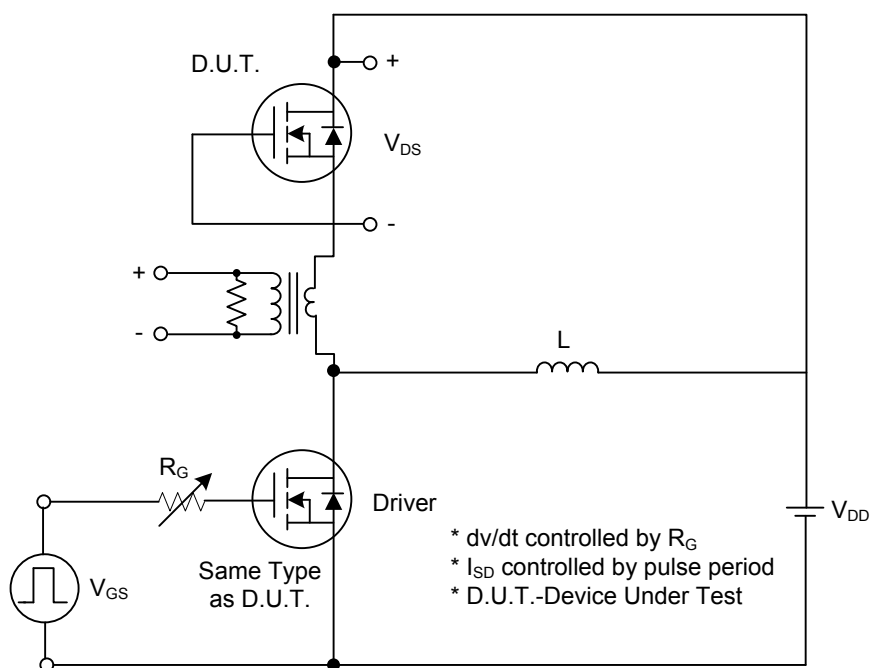
PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	3.47	$^\circ\text{C}/\text{W}$

■ **ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

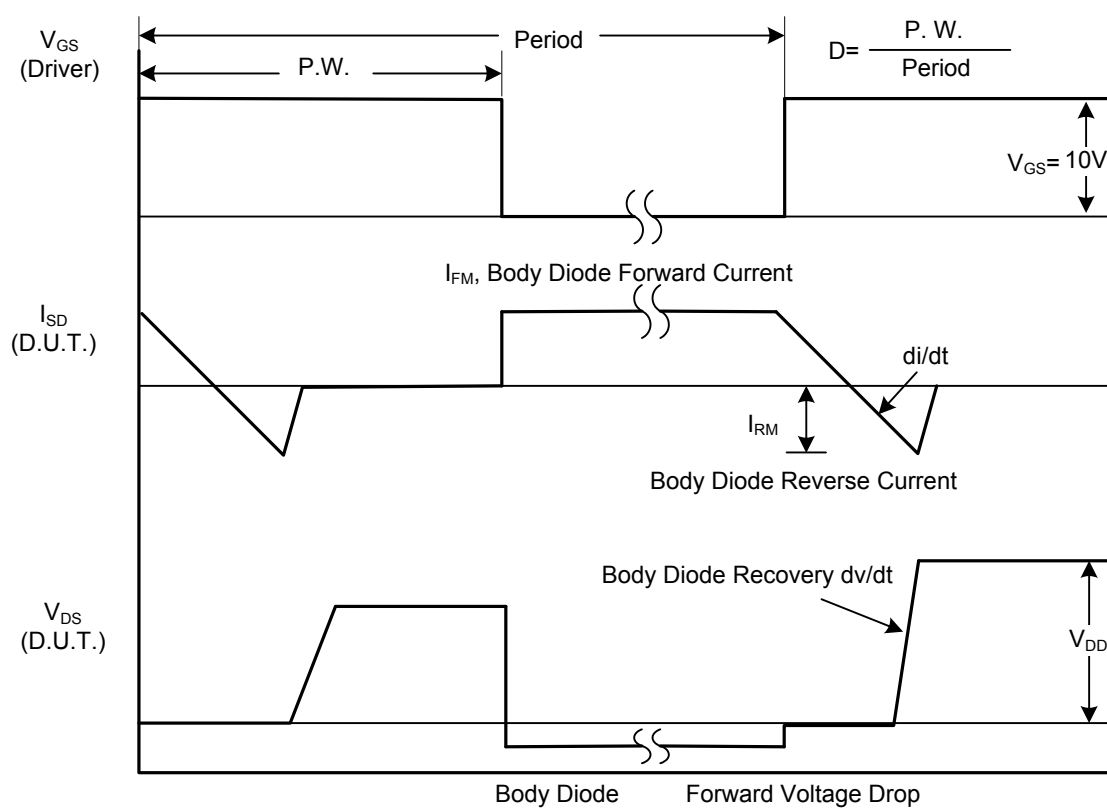
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
			V _{DS} =600V, V _{GS} =0V, T _C =125°C			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =30V, V _{DS} =0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} =0V			-100	nA
Breakdown Voltage Temperature Coefficient		ΔBV _{DSS} /ΔT _J	I _D =250μA, Referenced to 25°C		0.6		V/°C
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.5		4.5	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10 V, I _D =2.2A			2.5	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		477	575	pF
Output Capacitance		C _{OSS}			50	75	pF
Reverse Transfer Capacitance		C _{RSS}			5.82	11	pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	V _{DD} = 300V, I _D = 4.0A, R _G = 25Ω (Note 1, 2)		45		ns
Turn-On Rise Time		t _R			38		ns
Turn-Off Delay Time		t _{D(OFF)}			98		ns
Turn-Off Fall Time		t _F			30		ns
Total Gate Charge		Q _G	V _{DS} = 480V,I _D = 4.0A, V _{GS} = 10V (Note 1, 2)		17.7		nC
Gate-Source Charge		Q _{GS}			6		nC
Gate-Drain Charge		Q _{GD}			3		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} = 0V, I _S = 4.4A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				4.4	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				17.6	A

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
 2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

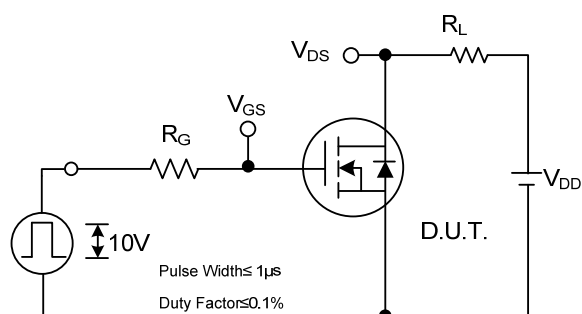


Peak Diode Recovery dv/dt Test Circuit

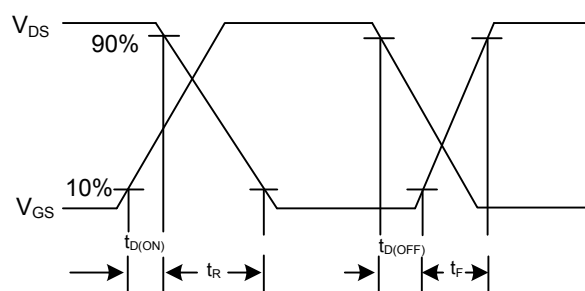


Peak Diode Recovery dv/dt Waveforms

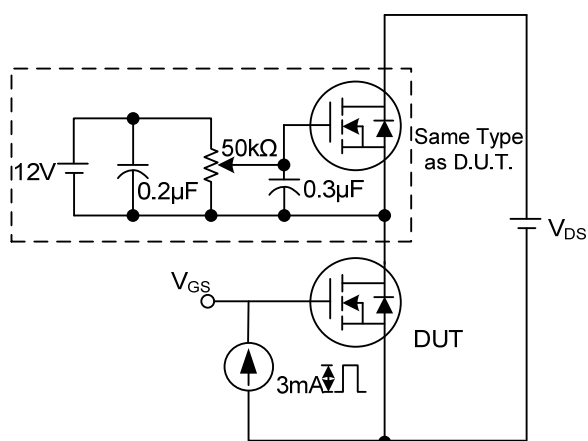
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



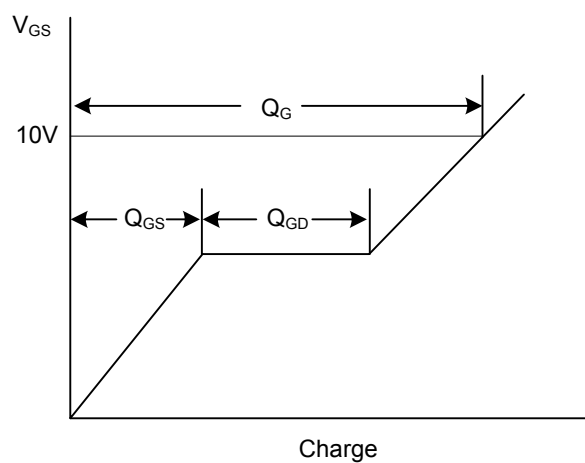
Switching Test Circuit



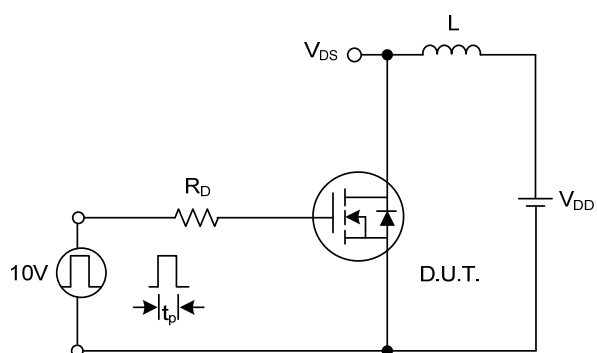
Switching Waveforms



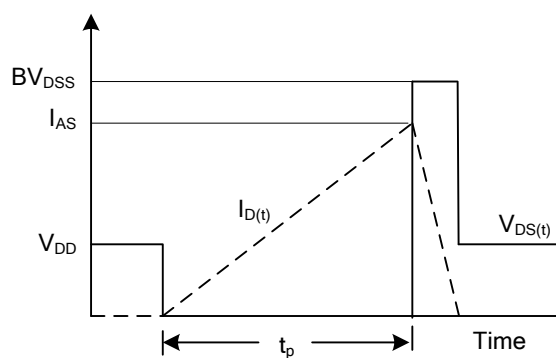
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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